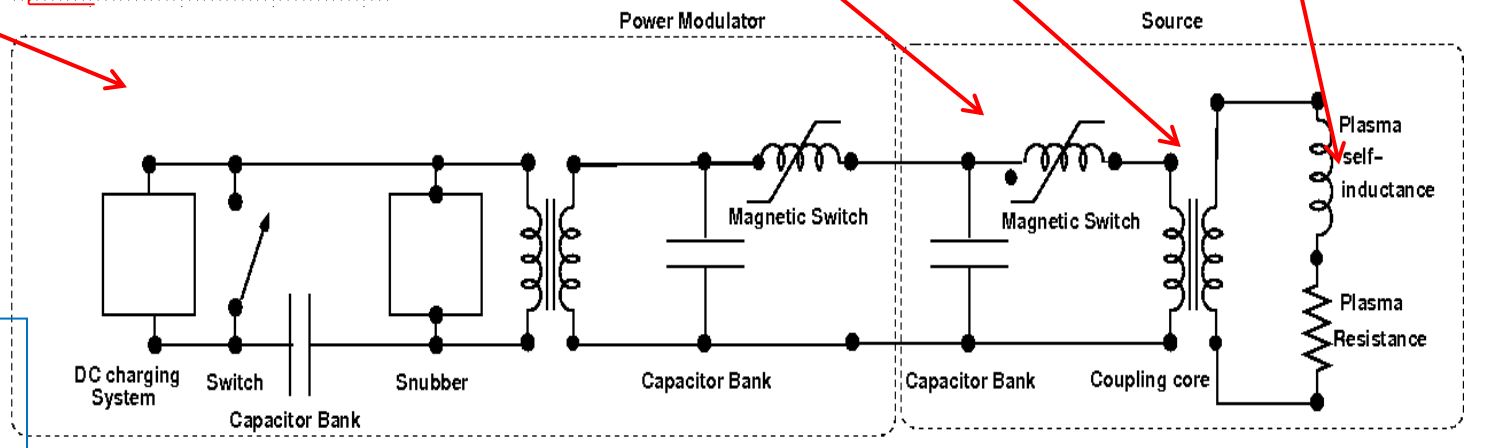
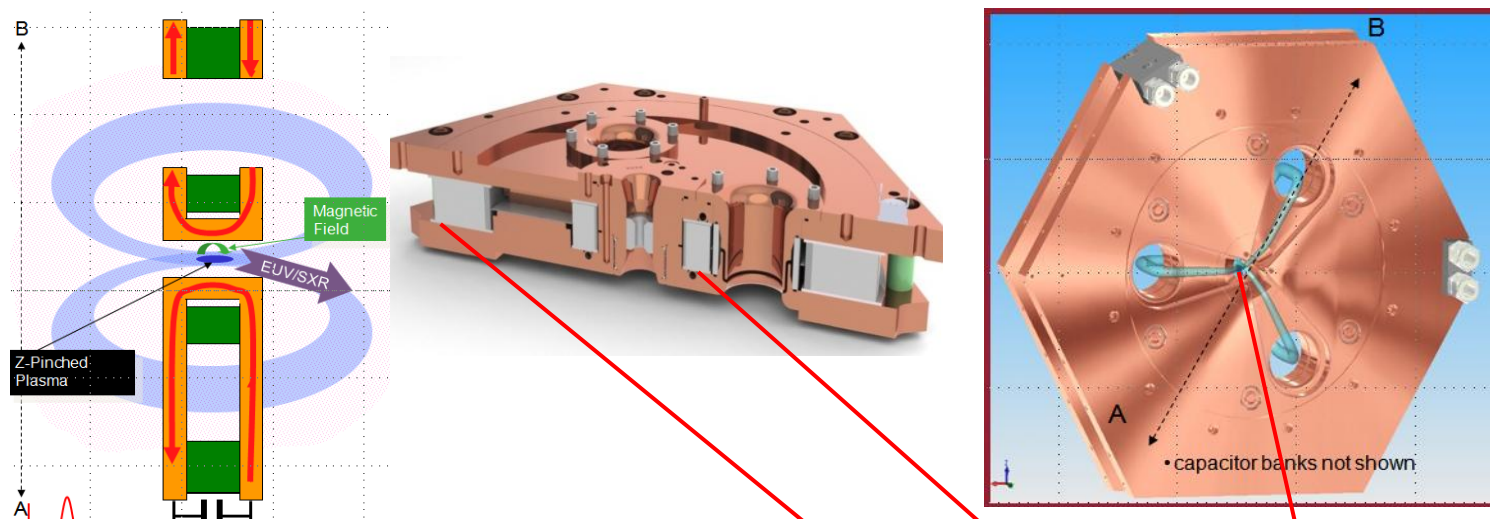


Energetiq Technology Inc. produces a variety of light sources. This poster will review the physics of these products (and some proposed devices), with an emphasis on applications. The technology to be described includes the basic EQ-10 at 13 nm wavelength, and related devices including higher power, high pulse rate, and proposed high brightness concepts, and the 2.88 nm source for water window microscopy derived from the EQ-10. In addition, we will present a summary of the physics and applications of the family of products based on Energetiq's Laser Driven Light Source technology.

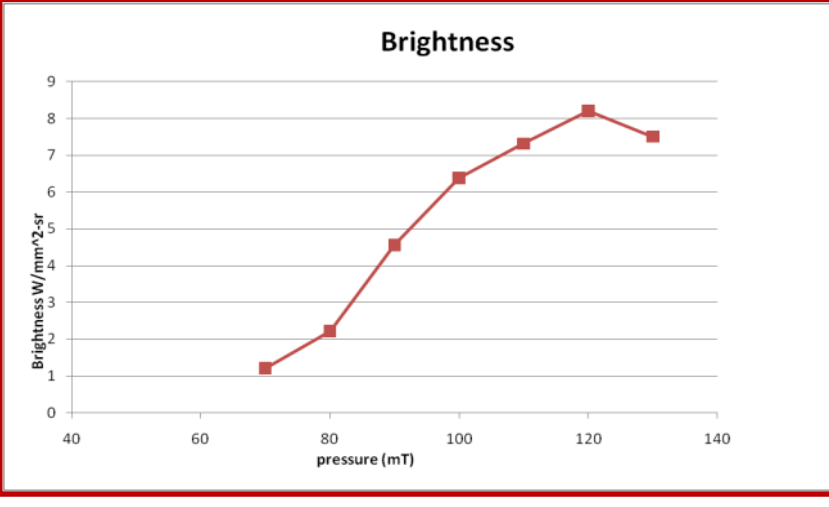
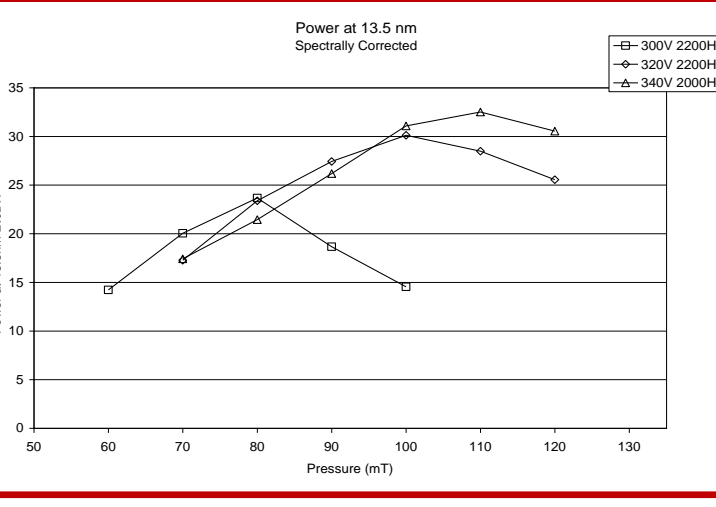
Electrode-less Z-Pinch™



Inductively driven, electrode-less Z-pinch – integrated magnetic switch.

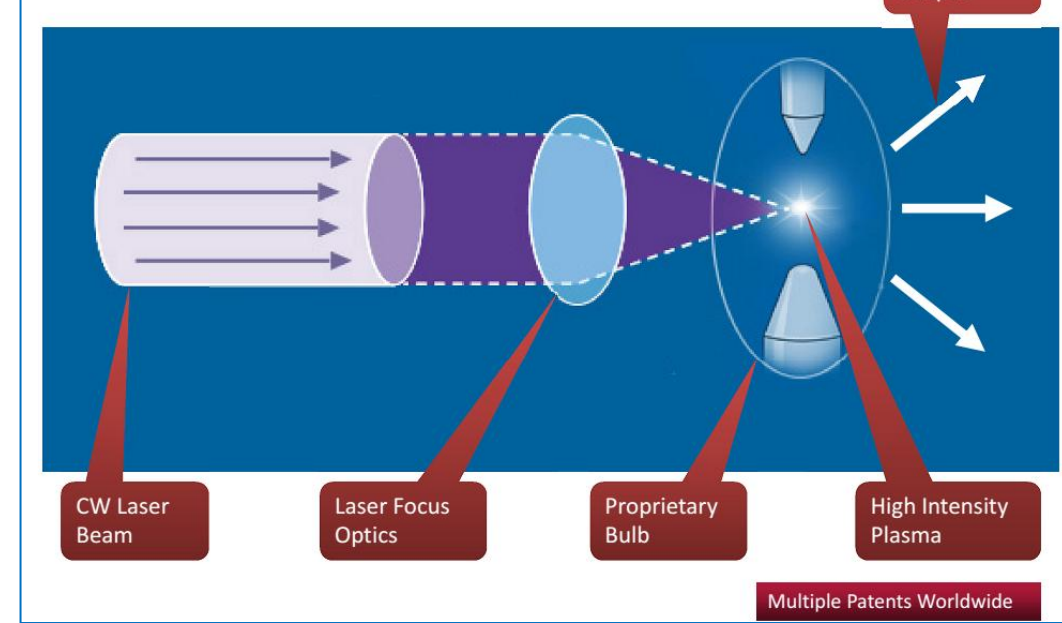
20 W of 13.5nm ±1% Power in 2π
~8 W/mm2-sr brightness
>95% uptime; 24/7 operation

Industry standard source for EUV infrastructure R&D, Inspection, Resist development, Outgassing, Mirror testing, &etc...



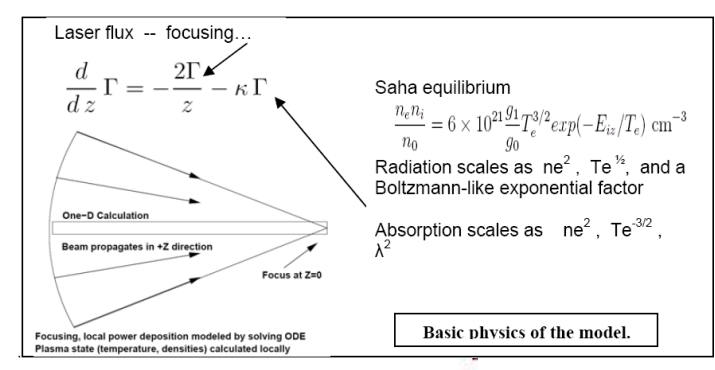
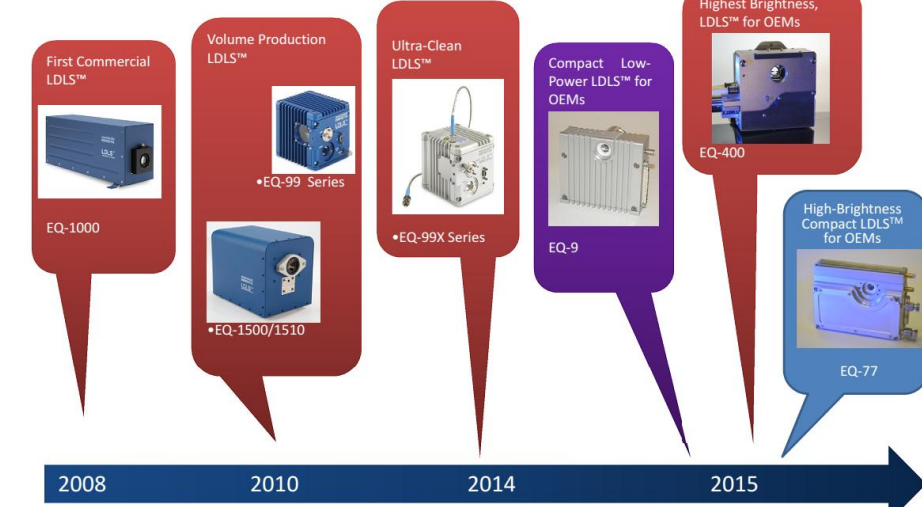
Vis/UV Light Sources - LDLS™

Laser-Driven Light Source: Principle of Operation



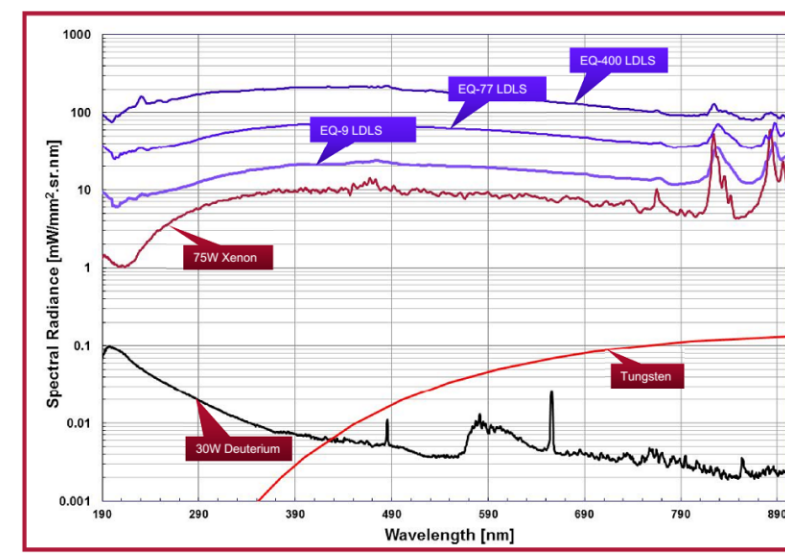
Spectral brightness scales with laser power (unlike arc lamp, where plasma increases in size, limiting brightness).

LDLS™ History of Innovation



Applications

- Analytical Spectroscopy
- HPLC, AA, UV-Vis
- Materials Characterization
- Environmental Analysis
- Hyperspectral Imaging
- Gas Phase Measurements
- Advanced Microscopes
- Endoscopes...

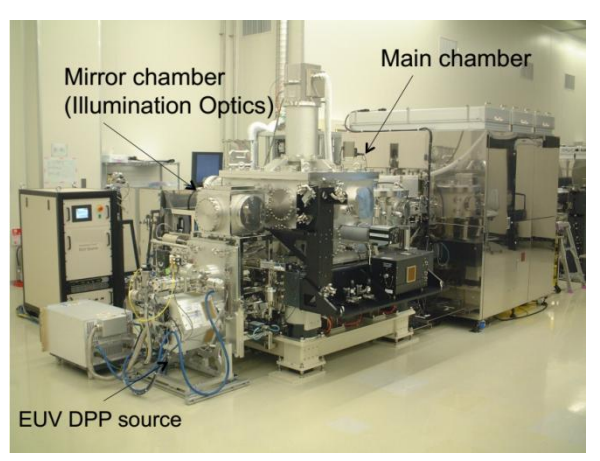


Application – UV Microscopy

250x improvement in exposure times compared to UV LED. Allows direct mapping of protein concentrations.[11]



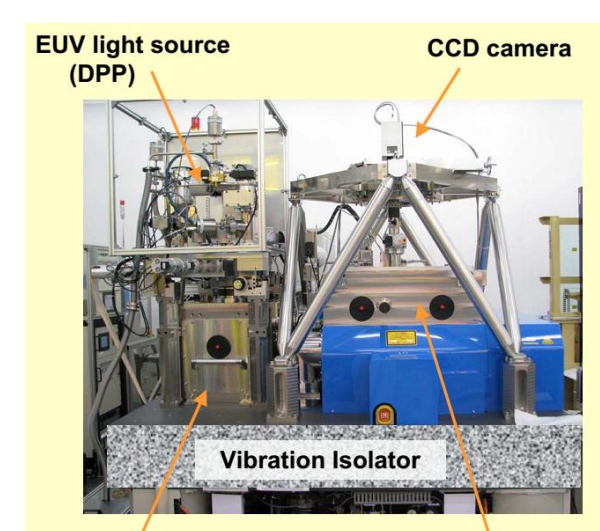
Applications and Installations ~ 25 worldwide



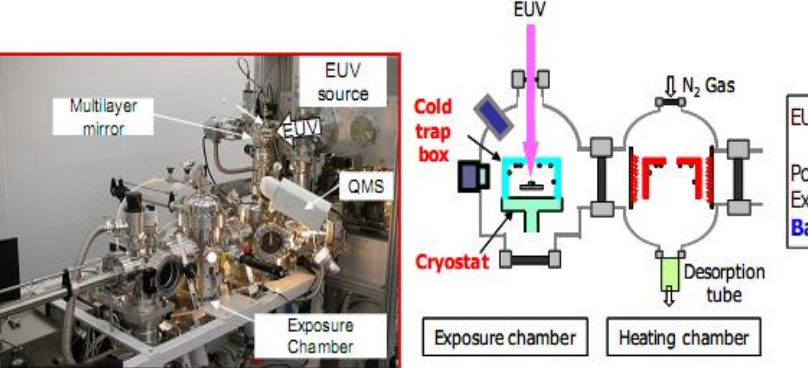
Lasertec/EIDEC mask inspection tool [1]



Flood Exposure system installed at Osaka University [3]



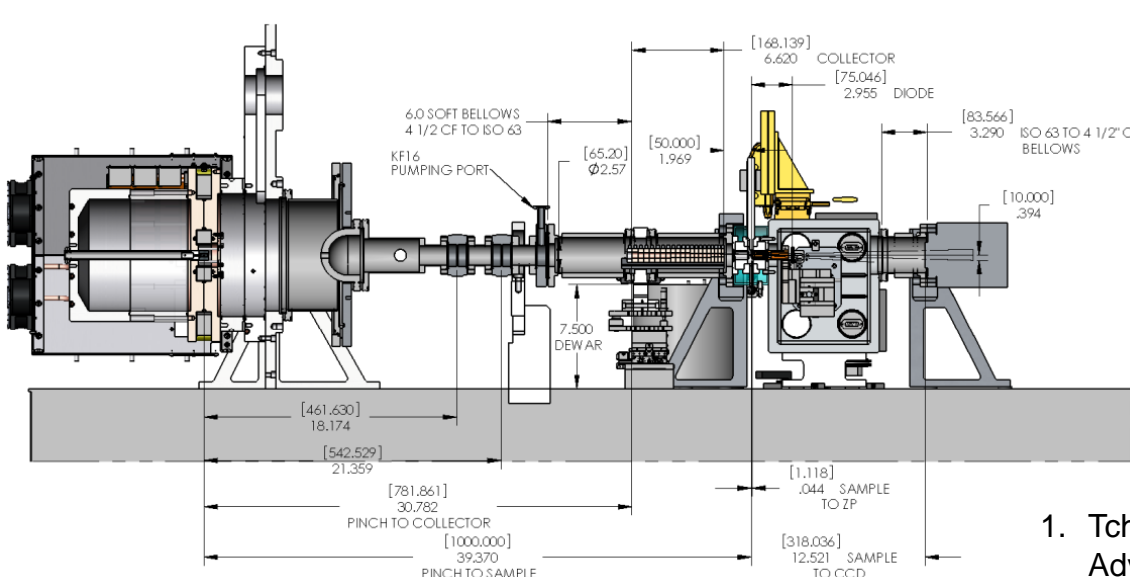
Actinic mask inspection SELETE [2]



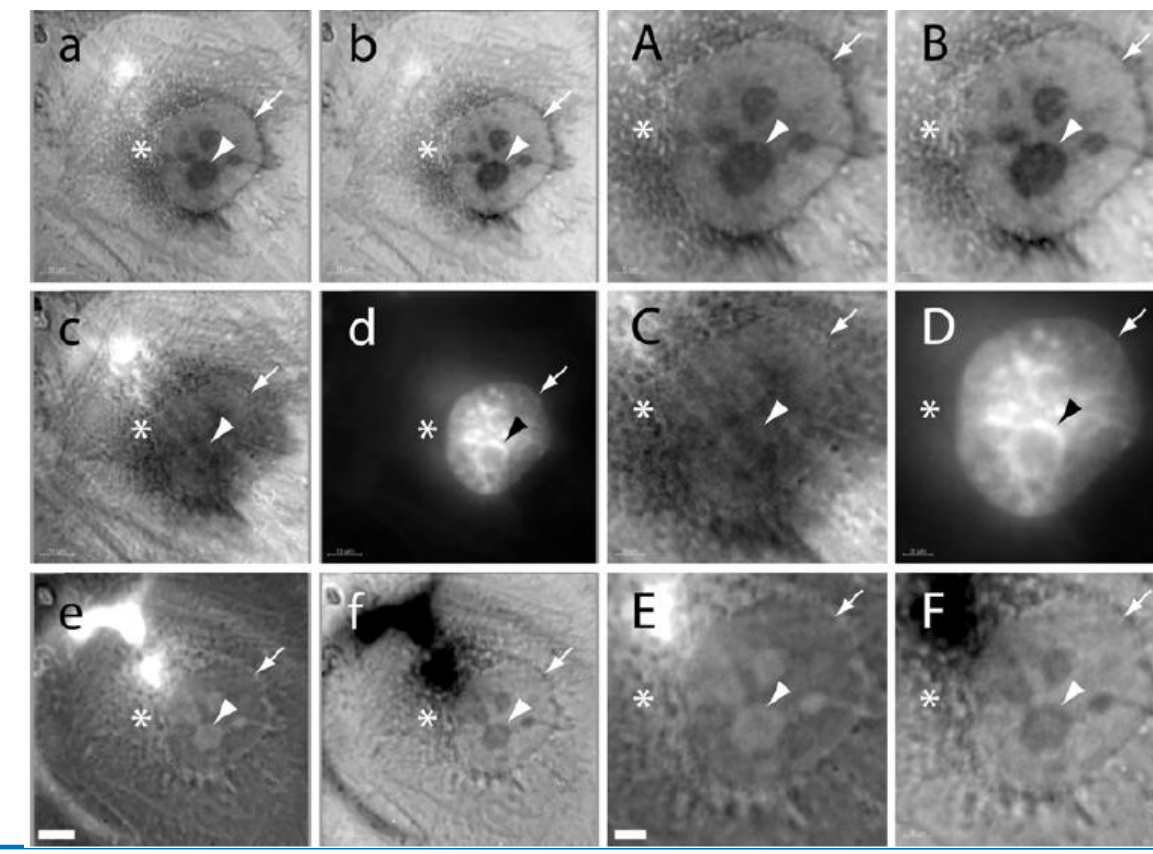
EUV Technology Outgassing Tool Installed at IMEC [4]



LithoTech Outgassing Tool installed at Selete [5]



Water Window microscope (2.88 nm) at Energetiq[9]



Advanced Concepts[8]

Modified Z-pinch: Scale frequency up, size, power down.

- Scale to a measured EQ-10 plasma
- Use FET switches instead of magnets for pulse shaping.
- Analyze pinch dynamics via scaling, dimensionality arguments.

Parameter	Existing	Proposed
Bore Diameter: mm	6	1
Length: mm	3	2
Pulse Rate: Hz	2.50E+03	5.98E+04
Brightness: W/mm²·sr	4.5	180
Compressed Diameter: mm	0.4	0.027
Compression Ratio:	15	15
Uncompressed Ion Density	1.77E+21	3.53E+21
Bennett Current: A	6.64E+03	1.56E+03
Peak Current: A	1.08	1.05
Peak Current: A	6.99E+03	1.65E+03
Time to Reach Peak Current: s	2.51E-07	4.19E-08
Total Inductance: H	1.90E-08	9.49E-09
Resistance: H	9.87E-02	9.87E-02
Capacitance: F	2.38E-08	8.99E-08
Voltage: V	1000	400
Power to Plasma: W	4.21E+03	1.66E+03

Use Stable Electrodeless Z-Pinch to Make Cold, Dense Xe Plasma: Heat with Pulsed Laser

The target plasma conditions (density, temperature, charge state) can be tuned to optimize overall system performance. Laser focus determines plasma size.

Estimate the operating point for the target plasma

- Consider laser absorption as plasma heats.
- Use FLYCHK code to estimate parameters.

As laser pulse starts, cold plasma (5 eV, 1e19 cm⁻³) has short cooling distance + good cooling. As plasma heats, absorption remains good.

Estimate Output Brightness:

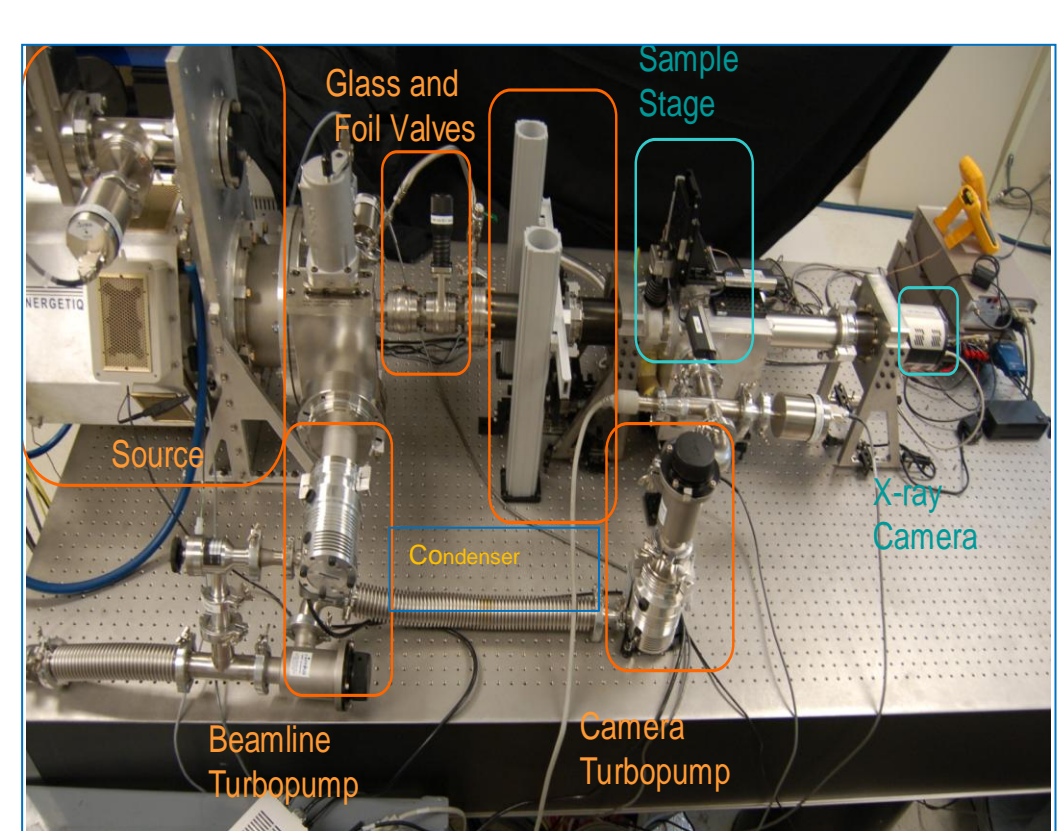
Band-Broad radiation ~ (N_eN_i)² (other stuff that should be roughly constant)

→ ratio of 18 pressures², after reabsorption

Usual 18 pressure 90-90 mtor; increase by factor of ~10

Expect ~ factor of 100 more intensity. FLYCHK says ~200

180W/mm² or seems readily achievable



References

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